

# Metal Reduction from Highly Viscose Microelectronics Fluids

Majid Entezarian, Mitsuaki Kobayyashi, Chih Ying Chien, and Sandeep Singh Solventum Purification and Filtration, St. Paul, MN, USA

# Reprint with permission:

Proceedings Volume 13428, Advances in Patterning Materials and Processes XLII; 134282U (2025) <a href="https://doi.org/10.1117/12.3057201">https://doi.org/10.1117/12.3057201</a>

Event: SPIE Advanced Lithography + Patterning, 2025, San Jose, California, United States

# Metal Reduction from Highly Viscose Microelectronics Fluids

Majid Entezarian, Ph.D.<sup>1</sup>, Mitsuaki Kobayashi<sup>2</sup>, Chih Ying Chien, Ph.D.<sup>2</sup>, and Sandeep Singh, Ph.D.<sup>3</sup>
<sup>1</sup>Solventum, Purification and Filtration, 400 Research Parkway, Meriden, CT 06450, USA,
<sup>2</sup>Solventum, Purification and Filtration, 3-8-8, Minami Hashimoto, Chuo-ku, Sagamihara-shi, Kanagawa, Japan, 252-0253
<sup>3</sup>Solventum, Purification and Filtration, 2510 Conway Ave E, Maplewood, MN, 55145, USA
Corresponding authors: mentezarian@solventum.com and ssingh2@solventum.com

#### **ABSTRACT**

Various chemicals are used in photo-resists applications that have high viscosity. The metal content of these chemicals is of concern as they may contaminate the wafers during the processing and post processing by diffusing into the circuit components and affecting their performance over time.

The high viscosity of these chemicals results in high pressure drop across porous media such as membranes or monoliths. A new monolith microstructure has been developed allowing to process high viscosity fluids for metal reduction while maintaining high flow rates.

Experiments were performed to compare the flow rates and the metal reduction of the monoliths. In addition, the metal reduction capacities were compared. The results of metal reduction will be presented using the new monolith.

**Keywords:** Purification, Filtration, Defect reduction, Photoresist, High Purity Chemicals

#### 1. INTRODUCTION

High Purity fluids and gels are needed for various microelectronics applications <sup>[1]</sup>. These fluids could be high polymer solutions, epoxies, amines, photoresists, masks, barrier layers, etc. The low metal content of these fluids is of prime importance as the metals interfere with the main functions such as conductivity, resistance, capacitance, dielectric, or others<sup>[2]</sup>. Purification methods such as distillation cannot by employed for these high solid solutions as it leads to phase separation. The Ion exchange technology can be used. However, the packed bed of the ion-exchange beads is not very efficient, needing a large volume of beads and difficult to reach low parts per trillion. There are also membranes with grafted ion-exchange properties that can be used for removing metals. These membranes have pore sizes that are smaller than one micron. These structures are associated with high pressure drops when used for high viscosity fluids. The flow of high viscosity fluids through depth porous structures has been studies<sup>[3]</sup>. The combination of viscose flow in porous structures with ion exchange properties are not well known. The objective of this study was to develop structures that can operate high viscosity fluids at high flow rates while efficiently removing metal ions.

#### 2. EXPERIMENTAL PROCEDURES

Two ion-exchange chemistries were made into monoliths with different pore structures. The two ion-exchange chemistries were sulphonic acid and amino phosphate. The sulphonic acid chemistry is a strong cationic ion-exchange with H ion for exchange denoted as SCP while the ammino phosphate is a

chelating chemistry also with H ions for exchange denoted as APP. These chemistries were made into monoliths with two different densities. One monolith would be denser with smaller mean pore size known as MIP-UHP SCP or MIP-UHP APP and the other less dense with larger mean pore size known as MIP-HV SCP and MIP-HV APP. These structures were subjected to fluids at various viscosities and upstream pressures and measured the flow rates at each viscosity and pressure. In addition, PGMEA was spiked with common metals of interest in the microelectronics manufacturing and passed through the monolith and measured the metal removal capability of the two chemistries. The metal content of the spiked and the purified samples were analyzed using ICP-MS.

### 2. RESULTS AND DISCUSSION

The results of the flow rate at various viscosity and various pressure setting are listed in figure 1. The samples listed as UHP are tighter media and a typical ion-exchange capacity of 450 mEq per 10" cartridge while, the HV samples have more open structures with a typical ion-exchange capacity of 250 mEq per 10" cartridge.

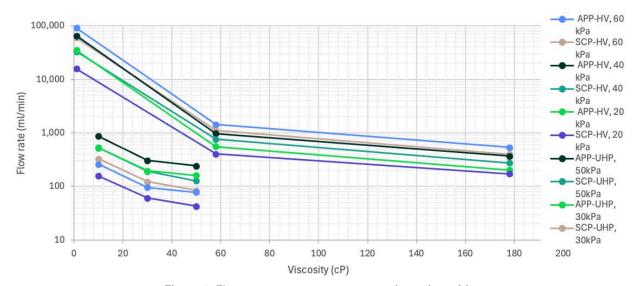


Figure 1. Flow rate versus pressure at various viscosities

The effect of increasing viscosity on flow rate is significant. The relationship between these two factors is a negative exponential meaning that the flow rate will be reduced exponentially by increasing the viscosity. For the UHP grade, the flow rate at viscosities larger than 50 cP is not practical as the flow rate drops to less than 100 ml/min per 10" cartridge. In comparison, the HV grades can operate at 10 times faster flow rate at comparable upstream pressures. For fluids with viscosities higher than 50 cP, both the SCP and APP in the UHP format did not result meaningful flow rate for a 10" cartridge.

Higher flow rates are seen when the pressure across the monoliths is increased across of any monolith grade. However, the increase in flow rate because of increase in pressure drop is not as pronounced as lowering the viscosity. There is a linear relationship between the increase pressure drop and the flow rate. This behavior is shown in figure 2.

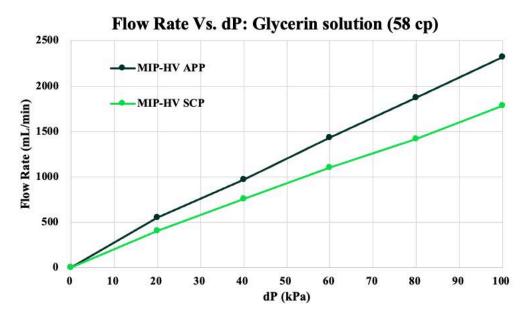


Figure 2. The Flow rate versus pressure drop across MIP-HV SCP and APP monoliths at 58 cP

## **Metal Removal Efficiency:**

The metal removal efficiency of both structures with either chemistry was assessed. The results are summarized in figure 3 through 6. Both MIP HV and MIP UHP demonstrated a high removal efficiency of >90% for total metal ion contamination in PGMEA. The results of metal removal using the low-density MIP HV with the two chemistries of SCP and APP, exhibit varying affinities towards different metals. The APP chemistry is more effective in removing heavier metals with higher valance (e.g. Mg, Ca) while the SCP chemistry shows more effective at removal of lighter metals that are monovalent. The denser structure of MIP UHP with both chemistry shows very effective removal of all metals.

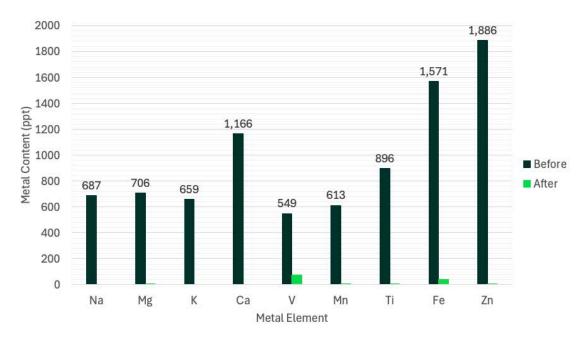


Figure 3. Metal removal form PGMEA by single pass using MIP-HV SCP grade (2.0 L/min)

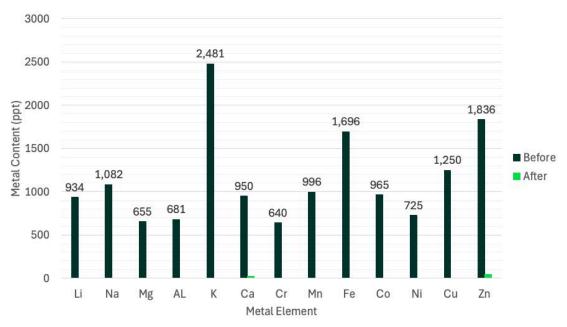


Figure 4. Metal removal form PGMEA by single pass using MIP-UHP SCP grade (0.7 L/min)

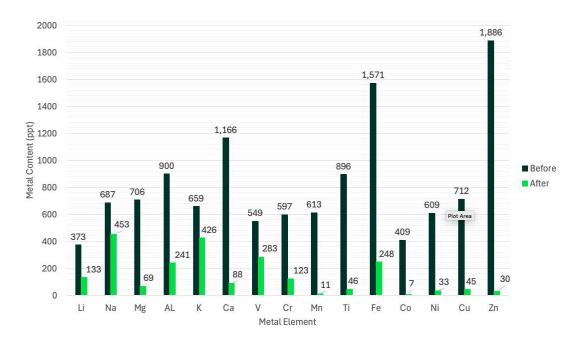


Figure 5. Metal removal form PGMEA by single pass using MIP-HV APP grade (2.0 L/min)

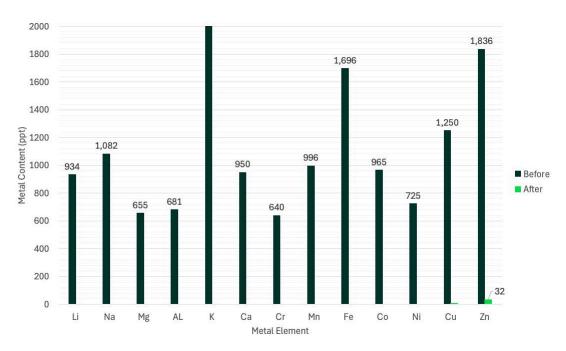


Figure 6. Metal removal form PGMEA by single pass using MIP-UHP APP grade (0.7 L/min)

## **CONCLUSIONS**

The high viscosity fluids are used in the manufacturing process of the integrated circuits. These fluids have metal impurities which if not removed could cause functional and reliability issues. There are very limited options for removing metals from these fluids. Two ion exchange chemistries were made into depth porous structures that could flow reasonably well and reducing metal content. Both ion exchange chemistries of strong sulphonic acid (SCP) and ammino-phosphate (APP) were effective for removing metals from PGMEA. The SCP chemistry showed capability for removal of most metals while the APP chemistry was more efficient at removing the heavier metals that are multi-valent.

#### REFERENCES

- [1] <u>Majid Entezarian</u> and <u>Bob Geiger</u> "The effect of materials selection on metals reduction in propylene glycol methyl ether acetate, PGMEA", Proc. SPIE 9778, Metrology, Inspection, and Process Control for Microlithography XXX, 97783H (8 March 2016); <a href="https://doi.org/10.1117/12.2220044">https://doi.org/10.1117/12.2220044</a>.
- [2] Majid Entezarian, Kristy Bellview, and Sandeep Singh "Characterization of nylon membranes for nano-particle filtration", Proc. SPIE 12957, Advances in Patterning Materials and Processes XLI, 1295728 (9 April 2024); https://doi.org/10.1117/12.3011159.
- [3] Victor C. Ibezim, Robert J. Poole, David J.C. Dennis "Viscoelastic fluid flow in microporous media" Journal of Non-Newtonian Fluid Mechanics, Volume 296, 2021, https://doi.org/10.1016/j.jnnfm.2021.104638.

# Metal Reduction from Highly Viscose Microelectronics Fluids

**Technical Information:** The technical information, guidance, and other statements contained in this document or otherwise provided by Solventum are based upon records, tests, or experience that Solventum believes to be reliable, but the accuracy, completeness, and representative nature of such information is not guaranteed. Such information is intended for people with knowledge and technical skills sufficient to assess and apply their own informed judgment to the information. No license under any Solventum or third party intellectual property rights is granted or implied with this information.

Product Selection and Use: Many factors beyond Solventum's control and uniquely within user's knowledge and control can affect the use and performance of a Solventum product in a particular application. As a result, customer is solely responsible for evaluating the product and determining whether it is appropriate and suitable for customer's application, including conducting a workplace hazard assessment and reviewing all applicable regulations and standards (e.g., OSHA, ANSI, etc.). Failure to properly evaluate, select, and use a Solventum product and appropriate safety products, or to meet all applicable safety regulations, may result in injury, sickness, death, and/or harm to property.

Warranty, Limited Remedy, and Disclaimer: Unless a different warranty is expressly stated on the applicable Solventum product packaging or product literature (in which case such express warranty governs), Solventum warrants that each Solventum product meets the applicable Solventum product specification at the time Solventum ships the product. SOLVENTUM MAKES NO OTHER WARRANTIES OR CONDITIONS, EXPRESS OR IMPLIED, INCLUDING, BUT NOT LIMITED TO, ANY IMPLIED WARRANTY OR CONDITION OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR ARISING OUT OF A COURSE OF DEALING, CUSTOM, OR USAGE OF TRADE. If a Solventum product does not conform to this warranty, then the sole and exclusive remedy is, at Solventum's option, replacement of the Solventum product or refund of the purchase price.

Limitation of Liability: Except for the limited remedy stated above, and except to the extent prohibited by law, Solventum will not be liable for any loss or damage arising from or related to the Solventum product, whether direct, indirect, special, incidental, or consequential (including, but not limited to, lost profits or business opportunity), regardless of the legal or equitable theory asserted, including, but not limited to, warranty, contract, negligence, or strict liability.



Solventum Corporation 2510 Conway Avenue East St. Paul, MN 55144-1000

Phone 1-800-243-6894 1-203-237-5541 Web Solventum.com 3M Purification is now part of Solventum

© Solventum 2025. Solventum and the S logo are trademarks of Solventum or its affiliates. 3M, and the 3M logo are trademarks of 3M. Other trademarks are the property of their respective owners. 70-2016-0444-7